

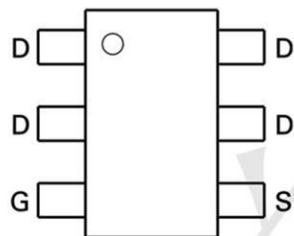
Product Summary

| $V_{(BR)DSS}$ | $R_{DS(on)}\text{MAX}$ | I_D |
|---------------|------------------------|-------|
| -30V | 60m Ω @-10 V | -4.1A |
| | 87m Ω @-4.5V | |

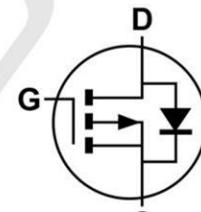
Application

- DC-DC Converters.
- Load Switch.
- Power Management.

Package and Pin Configuration



Circuit diagram



Equivalent Circuit

Marking: **TP 3P5**

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|---|-----------------|----------|------|
| Drain-Source Voltage | V_{DS} | -30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain Current | I_D | -4.1 | A |
| Power Dissipation | P_D | 350 | mW |
| Thermal Resistance from Junction to Ambient | $R_{\theta JA}$ | 357 | °C/W |
| Junction Temperature | T_J | 150 | °C |
| Storage Temperature | T_{stg} | -55~+150 | °C |

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

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| Parameter | Symbol | Test Condition | Min | Typ | Max | Units |
|---|-----------------------------|--|-----|-----------|-----|------------------|
| Static characteristics | | | | | | |
| Drain-source breakdown voltage | $V_{(\text{BR})\text{DSS}}$ | $V_{\text{GS}} = 0\text{V}, I_{\text{D}} = -250\mu\text{A}$ | -30 | | | V |
| Zero gate voltage drain current | I_{DSS} | $V_{\text{DS}} = -24\text{V}, V_{\text{GS}} = 0\text{V}$ | | -1 | | μA |
| Gate-source leakage current | I_{GSS} | $V_{\text{GS}} = \pm 20\text{V}, V_{\text{DS}} = 0\text{V}$ | | ± 100 | | nA |
| Drain-source on-resistance (note 1) | $R_{\text{DS}(\text{on})}$ | $V_{\text{GS}} = -10\text{V}, I_{\text{D}} = -4.1\text{A}$ | | 50 | 60 | $\text{m}\Omega$ |
| | | $V_{\text{GS}} = -4.5\text{V}, I_{\text{D}} = -3\text{A}$ | | 68 | 87 | $\text{m}\Omega$ |
| Forward transconductance (note 1) | g_{fs} | $V_{\text{DS}} = -5\text{V}, I_{\text{D}} = -4\text{A}$ | 5.5 | | | S |
| Gate threshold voltage | $V_{\text{GS}(\text{th})}$ | $V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = -250\mu\text{A}$ | -1 | -1.4 | -3 | V |
| Diode forward voltage (note 1) | V_{SD} | $I_{\text{S}} = -1\text{A}, V_{\text{GS}} = 0\text{V}$ | | | -1 | V |
| Dynamic characteristics (note 2) | | | | | | |
| Input capacitance | C_{iss} | $V_{\text{DS}} = -15\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$ | | 700 | | pF |
| Output capacitance | C_{oss} | | | 120 | | pF |
| Reverse transfer capacitance | C_{rss} | | | 75 | | pF |
| Switching Characteristics (note 2) | | | | | | |
| Turn-on delay time | $t_{\text{d}(\text{on})}$ | $V_{\text{GS}} = -10\text{V}, V_{\text{DS}} = -15\text{V}, R_{\text{L}} = 3.6\Omega, R_{\text{GEN}} = 3\Omega$ | | 8.6 | | ns |
| Turn-on rise time | t_{r} | | | 5.0 | | ns |
| Turn-off delay time | $t_{\text{d}(\text{off})}$ | | | 28.2 | | ns |
| Turn-off fall time | t_{f} | | | 13.5 | | ns |



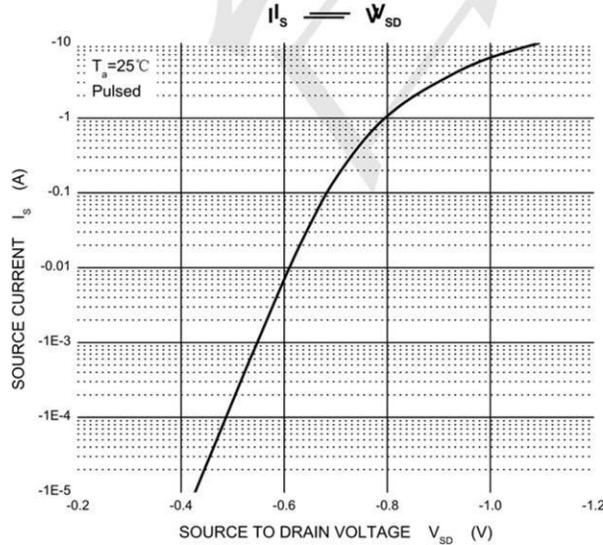
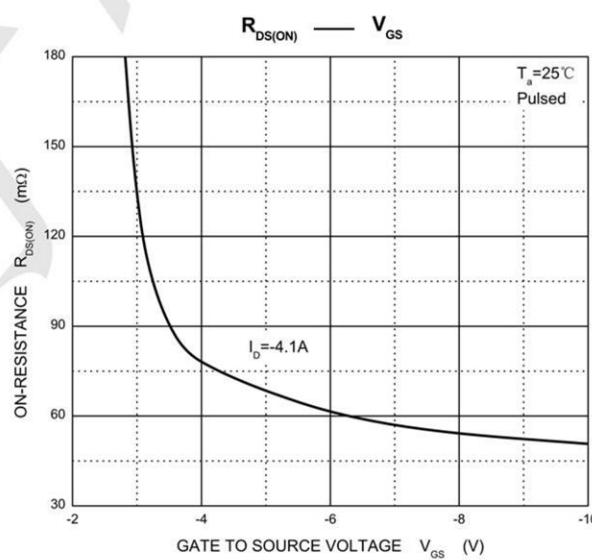
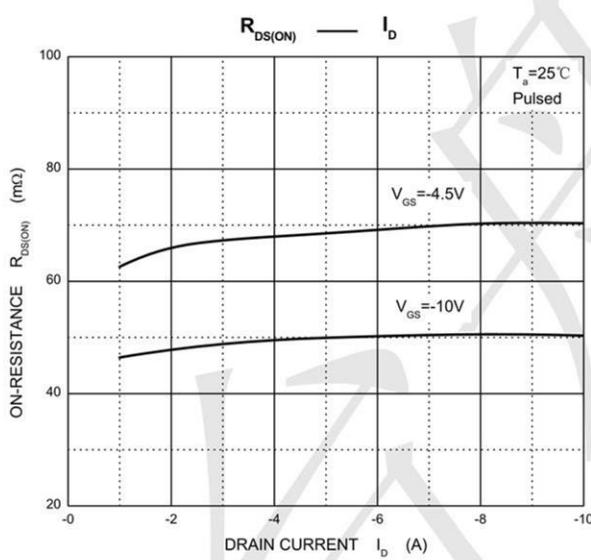
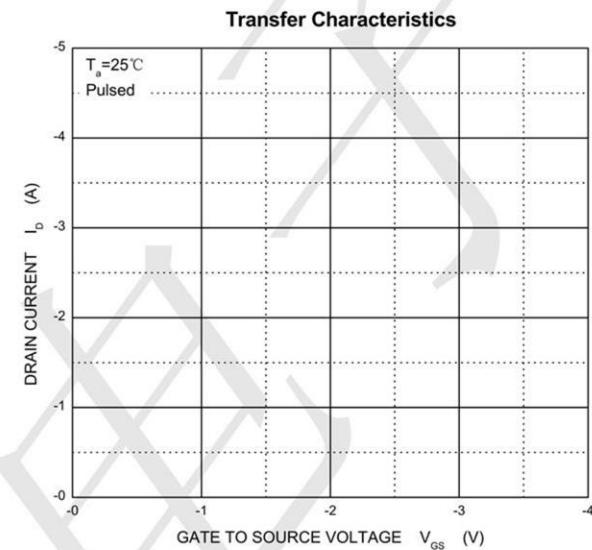
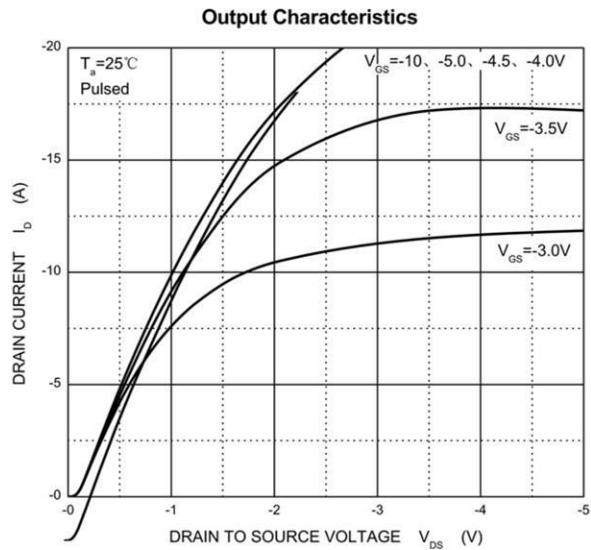
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TPM30V5PS6-3

30V P-CHANNEL ENHANCEMENT MODE MOSFET

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Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)





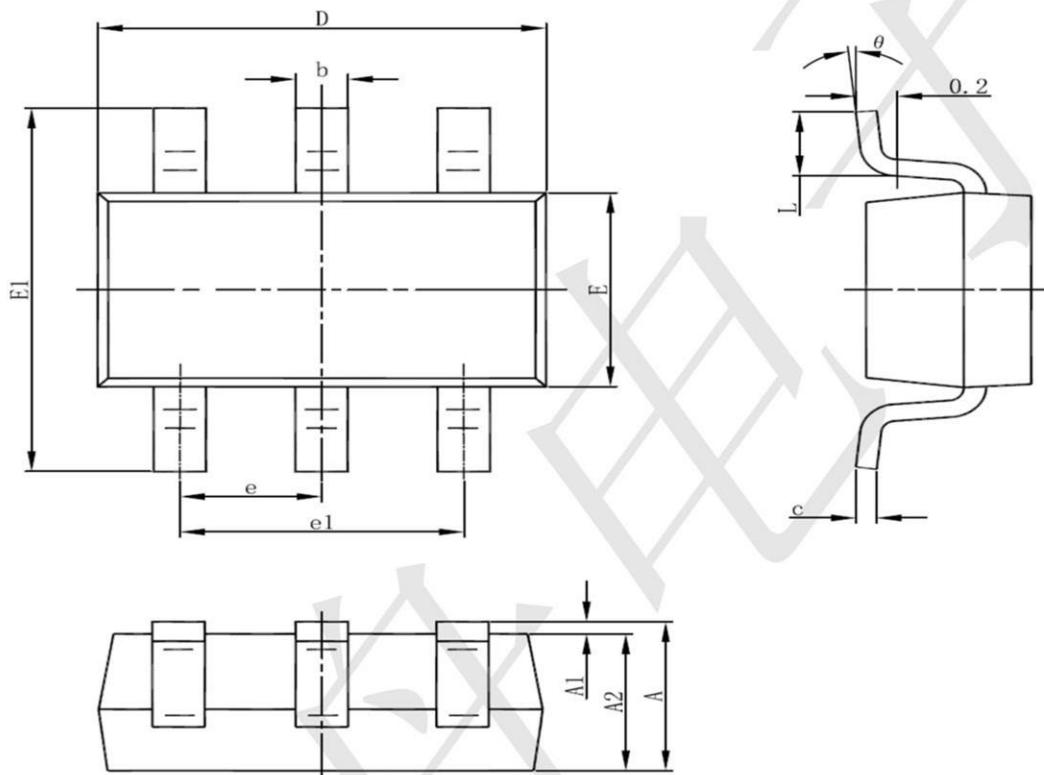
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TPM30V5PS6-3

30V P-CHANNEL ENHANCEMENT MODE MOSFET

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SOT23-6 Package Information



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 1.050 | 1.250 | 0.041 | 0.049 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 1.050 | 1.150 | 0.041 | 0.045 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.100 | 0.200 | 0.004 | 0.008 |
| D | 2.820 | 3.020 | 0.111 | 0.119 |
| E | 1.500 | 1.700 | 0.059 | 0.067 |
| E1 | 2.650 | 2.950 | 0.104 | 0.116 |
| e | 0.950(BSC) | | 0.037(BSC) | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.300 | 0.600 | 0.012 | 0.024 |
| θ | 0° | 8° | 0° | 8° |